



General Description

The MAX2667/MAX2669 high-gain, low-noise amplifiers (LNAs) are designed for GPS L1, Galileo, and GLONASS applications. Designed in Maxim's advanced SiGe process, the devices achieve a high gain and our lowest noise figure, while maximizing the input-referred 1dB compression point and the 3rd-order intercept point.

The devices operate from a +1.6V to +3.3V single supply. The MAX2667 is optimized for low current. The MAX2669 is optimized for high linearity. The shutdown feature in the device reduces the supply current to be less than $10\mu A$. The devices are available in a very small, lead-free, RoHS-compliant, $0.86mm \times 1.26mm \times 0.65mm$ wafer-level package (WLP).

Applications

Automotive Navigation

Location-Enabled Mobile Devices

Telematics (Asset Tracking and Management)

Personal Navigation Devices (PNDs)

Cellular Phones with GPS

Notebook PCs/Ultra-Mobile PCs

Recreational, Marine Navigation

Avionics

Watches

Features

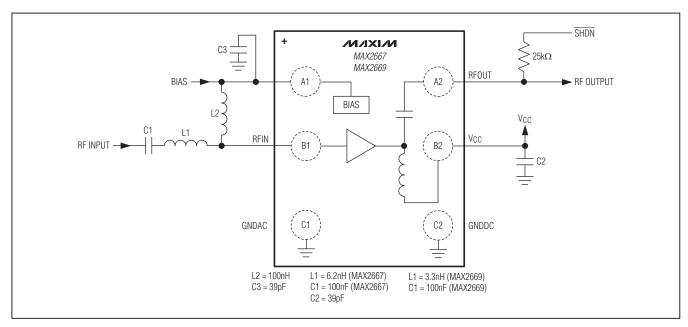
- ◆ 19dB High-Power Gain (MAX2667)
- ♦ Ultra-Low Noise Figure: 0.65dB
- ♦ Integrated 50Ω Output Matching Circuit
- ♦ Low 4.1mA Supply Current (MAX2667)
- ♦ Wide 1.6V to 3.3V Supply Voltage Range
- ♦ Low Bill of Materials: Two Inductors, Three Capacitors, and One Resistor
- ♦ Small Footprint: 0.86mm x 1.26mm
- ♦ Thin Profile: 0.65mm
- ♦ 0.4mm-Pitch Wafer-Level Package (WLP)

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX2667EWT+T	-40°C to +85°C	6 WLP
MAX2669EWT+T	-40°C to +85°C	6 WLP

+Denotes a lead(Pb)-free/RoHS-compliant package. T = Tape and reel.

Typical Application Circuit



Maxim Integrated Products 1

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

VCC to GND0.3V to +3.6V	Maximur
RFOUT and BIAS to GND0.3V to (Operating V _{CC} + 0.3V)	Operatir
Maximum RF Input Power+5dBm	Junction
Continuous Power Dissipation (T _A = +70°C)	Storage
WLP (derates 10.5mW/°C above +70°C)840mW	Solderin

Maximum Current into RF Input	10mA
Operating Temperature Range	
Junction Temperature	+150°C
Storage Temperature Range	65°C to +160°C
Soldering Temperature (reflow) (Note 1)	+260°C

Note 1: Refer to Application Note 1891: Wafer-level packaging (WLP) and its applications.



Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

(MAX2667/MAX2669 EV kit. $V_{CC} = 1.6V$ to 3.3V, no RF signals are applied, $T_{A} = -40$ °C to +85°C. Typical values are at $V_{CC} = 2.85V$ and $T_{A} = +25$ °C, unless otherwise noted.) (Note 2)

PARAMETER		CONDITIONS			MAX	UNITS
Supply Voltage			1.6	2.85	3.3	V
	OUDN 1: 1	MAX2667		4.1		то Л
Supply Current	SHDN = high	MAX2669		7.7		mA
	Shutdown mode, SHI	Shutdown mode, SHDN = low			10	μΑ
Digital Input Logic-High	TA = +25°C	TA = +25°C				V
Digital Input Logic-Low	T _A = +25°C	Γ _A = +25°C			0.45	V

AC ELECTRICAL CHARACTERISTICS

(MAX2667/MAX2669 EV kit. V_{CC} = 1.6V to 3.3V, f_{RFIN} = 1575.42MHz, T_A = -40°C to +85°C. Typical values are at V_{CC} = 2.85V and T_A = +25°C, unless otherwise noted.) (Note 2)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
RF Frequency	L1 band			1575.42		MHz
	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	MAX2667	15.0	19.5		
Dawar Cain	VCC = 2.85V	MAX2669	14.6	17.7		مار ا
Power Gain	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	MAX2667	14.8	19.4		dB
	VCC = 1.6V	MAX2669	14.3	17.6		1
Naisa Figura		Vcc = 1.8V		0.65		٩D
Noise Figure		$V_{CC} = 3.3V$		0.65		dB
In-Band 3rd-Order Input	(NI=+= O)	MAX2667		-3.5		dBm
Intercept Point	(Note 3)	MAX2669		+4.5		
Out-of-Band 3rd-Order Input	(Nata 4)	MAX2667		+2.5		dBm
Intercept Point	(Note 4)	MAX2669		+8		
Innut 1dD Compression Daint	(Nata E)	MAX2667		-12.5		-ID
Input 1dB Compression Point	(Note 5)	MAX2669		-10		dBm
Input Return Loss				10		dB
Output Return Loss				15		dB
Reverse Isolation				30		dB

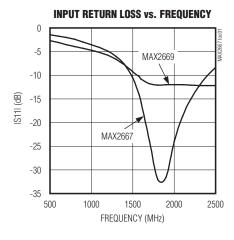
AC ELECTRICAL CHARACTERISTICS (continued)

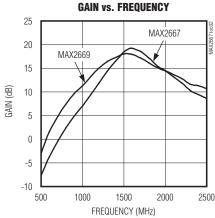
(MAX2667/MAX2669 EV kit. V_{CC} = 1.6V to 3.3V, f_{RFIN} = 1575.42MHz, T_A = -40°C to +85°C. Typical values are at V_{CC} = 2.85V and T_A = +25°C, unless otherwise noted.) (Note 2)

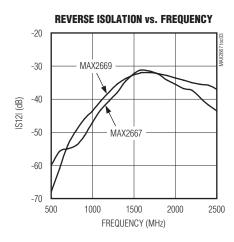
- Note 2: Min and max limits guaranteed by test at $T_A = +25^{\circ}C$ and guaranteed by design and characterization at $T_A = +40^{\circ}C$ and $T_A = +85^{\circ}C$.
- Note 3: Measured with the two tones located at 1MHz and 2MHz offset from the center of the GPS band with -30dBm/tone for MAX2667 and -27dBm/tone for MAX2669.
- Note 4: Measured with input tones at 1713MHz (-25dBm) and 1851MHz (-49dBm).
- Note 5: Measured with a tone located at 5MHz offset from the center of the GPS band.

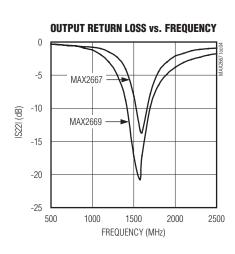
Typical Operating Characteristics

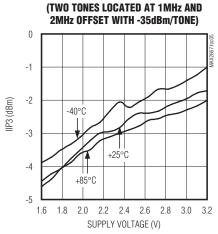
(MAX2667/MAX2669 EV kit. Typical values are at V_{CC} = 2.85V, f_{RFIN} = 1575.42MHz, T_A = +25°C, unless otherwise noted.)





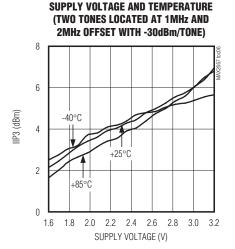






MAX2667 IN-BAND IIP3 vs.

SUPPLY VOLTAGE AND TEMPERATURE

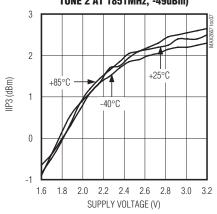


MAX2669 IN-BAND IIP3 vs.

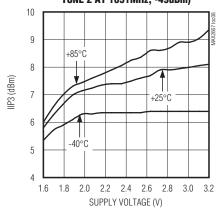
Typical Operating Characteristics (continued)

(MAX2667/MAX2669 EV kit. Typical values are at $V_{CC} = 2.85V$, $f_{RFIN} = 1575.42MHz$, $T_A = +25^{\circ}C$, unless otherwise noted.)

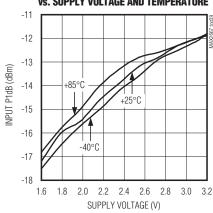
MAX2667 OUT-OF-BAND IIP3 vs. SUPPLY VOLTAGE AND TEMPERATURE (TONE 1 AT 1713MHz, -25dBm; TONE 2 AT 1851MHz, -49dBm)



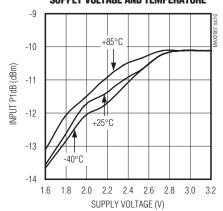
MAX2669 OUT-OF-BAND IIP3 vs. SUPPLY VOLTAGE AND TEMPERATURE (TONE 1 AT 1713MHz, -25dBm; TONE 2 AT 1851MHz, -49dBm)



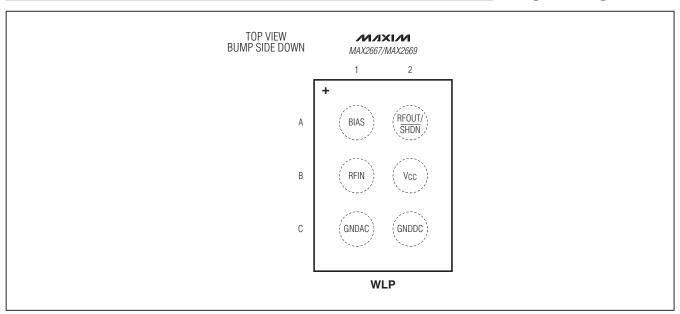
MAX2667 INPUT P1dB COMPRESSION vs. Supply voltage and temperature



MAX2669 INPUT P1dB COMPRESSION vs. SUPPLY VOLTAGE AND TEMPERATURE



Bump Configuration



Bump Description

BUMP	NAME	FUNCTION
A1	BIAS	Provides Bias for LNA Input. Connect to B1 (RFIN) through a high-value inductor (100nH), and bypass to ground close to the pin.
A2	RFOUT/SHDN	RF Output and \overline{SHDN} Logic Input. RFOUT is internally matched to 50Ω and has an internal DC-blocking capacitor. The \overline{SHDN} logic input is coupled through a $25k\Omega$ resistor.
B1	RFIN	RF Input. Connect to A1 through bias choke, and connect matching network and DC-blocking capacitor.
B2	Vcc	Supply Voltage. Bypass to ground with a capacitor close to the IC.
C1	GNDAC	Ground of the RF Path. Connect to the 2nd-layer PCB ground plane with a via next to the pin pad.
C2	GNDDC	Ground of Bias Circuit. Connect to the 2nd-layer PCB ground plane with a separate via from pin C1. Sharing a ground via with pin C1 might cause stability problems.

Detailed Description

The MAX2667/MAX2669 are LNAs designed for GPS L1, Galileo, and GLONASS applications. The devices feature a power-shutdown control mode to eliminate the need for an external supply switch. The devices achieve a high gain and an ultra-low noise figure.

Input and Output Matching

The devices require an off-chip input matching. Only an inductor in series with a DC-blocking capacitor is

needed to form the input matching circuit. The *Typical Application Circuit* shows the recommended input-matching network. These values are optimized for the best simultaneous gain, noise figure, and return loss performance. Tables 1 and 2 list typical device S parameters and Kf values. The devices integrate an on-chip output matching to 50Ω at the output, eliminating the need for external matching components. The value of the input coupling capacitor affects IIP3. A smaller coupling capacitor results in lower IIP3.



Shutdown

The devices include a shutdown feature to turn off the entire chip. Apply a logic-high to the SHDN pin to place the part in the active mode, and a logic-low to place the part in the shutdown mode.

Applications Information

A properly designed PCB is essential to any RF microwave circuit. Use controlled-impedance lines on all high-frequency inputs and outputs. Bypass VCC with

decoupling capacitors located close to the device. For long VCC lines, it may be necessary to add decoupling capacitors. Locate these additional capacitors further away from the device package. Proper grounding of the GND_ pins is essential. If the PCB uses a topside RF ground, connect it directly to the GND_ pins. For a board where the ground is not on the component layer, connect the GND_ pins to the board with multiple vias close to the package.

Table 1. MAX2667 Typical Device S-Parameter Values and K-Factor

FREQ. (MHz)	S11 MAG (dB)	S11 PHASE (Degrees)	S21 MAG (dB)	S21 PHASE (Degrees)	S12 MAG (dB)	S12 PHASE (Degrees)	S22 MAG (dB)	S22 PHASE (Degrees)	Kf
1000	-2.0	-47.7	6.0	-100.0	-47.5	-148.0	-1.0	-55.0	5.1
1100	-2.1	-48.6	7.4	-100.6	-45.7	-150.0	-1.0	-58.1	3.8
1200	-2.2	-51.6	9.6	-107.3	-42.9	-153.5	-1.4	-65.4	3.1
1300	-2.4	-55.0	12.0	-117.2	-39.6	-160.2	-2.1	-74.1	2.5
1400	-2.7	-58.6	14.0	-129.5	-37.0	-168.5	-3.6	-85.5	2.3
1500	-6.5	-61.9	16.2	-146.5	-34.1	178.5	-7.4	-100.0	2.8
1575	-4.3	-62.3	17.1	-164.2	-32.9	162.8	-15.3	-100.8	2.1
1600	-4.6	-61.6	17.3	-170.6	-32.8	156.6	-20.6	-78.9	2.0
1700	-5.4	-55.3	17.1	165.5	-32.5	136.5	-9.5	10.0	1.8
1800	-5.2	-49.8	15.7	145.8	-33.8	121.6	-4.5	-2.4	1.6
1900	-4.8	-47.3	13.9	135.2	-35.2	113.8	-2.7	-13.2	1.6
2000	-4.5	-46.7	12.7	127.3	-36.7	109.6	-1.8	-21.2	1.5

Table 2. MAX2669 Typical Device S-Parameter Values and K-Factor

FREQ. (MHz)	S11 MAG (dB)	S11 PHASE (Degrees)	S21 MAG (dB)	S21 PHASE (Degrees)	S12 MAG (dB)	S12 PHASE (Degrees)	S22 MAG (dB)	S22 PHASE (Degrees)	Kf
1000	-3.0	-57.0	10.8	-120.0	-43.0	-154.0	-1.3	-65.0	3.2
1100	-3.3	-58.2	11.6	-124.5	-42.1	-155.0	-1.6	-70.2	3.3
1200	-3.5	-60.0	13.4	-134.6	-39.3	-160.5	-2.4	-79.6	2.8
1300	-3.8	-62.3	14.9	-148.0	-37.2	-168.3	-4.0	-90.0	2.7
1400	-4.3	-63.3	15.9	-162.3	-35.4	-178.2	-7.3	-101.0	2.7
1500	-4.9	-62.0	16.6	-178.9	-33.9	171.0	-14.5	-100.6	2.6
1575	-5.3	-59.7	16.6	168.0	-33.5	161.7	-19.6	-26.0	2.5
1600	-5.4	-58.5	16.5	163.9	-33.6	157.5	-16.7	-6.0	2.5
1700	-5.5	-53.7	15.8	149.3	-33.6	148.3	-9.0	3.6	2.3
1800	-5.3	-50.3	14.7	136.8	-34.2	142.5	-5.7	-2.8	2.2
1900	-5.1	-48.0	13.4	130.0	-35.1	139.6	-4.0	-9.6	2.3
2000	-4.9	-46.3	12.7	123.9	-35.8	138.6	-3.0	-15.0	2.1

__/N/XI/N

Table 3. MAX2667 Typical Noise Parameters (VCC = 2.85V, TA = $+25^{\circ}C$)

FREQUENCY (MHz)	FMIN (dB)	lΓ ορτ l	IFOPTI ANGLE	R N (Ω)
1550	0.54	0.48	39.9	8.43
1560	0.55	0.48	40.2	8.42
1570	0.55	0.48	40.5	8.41
1575	0.55	0.48	40.7	8.41
1580	0.55	0.48	40.9	8.40
1590	0.55	0.48	41.2	8.39
1600	0.55	0.48	41.5	8.38

Table 4. MAX2669 Typical Noise Parameters (VCC = 2.85V, TA = $+25^{\circ}C$)

FREQUENCY (MHz)	FMIN (dB)	lΓορτί	IFOPTI ANGLE	R _N (Ω)
1550	0.57	0.29	76.1	4.53
1560	0.57	0.29	76.6	4.53
1570	0.57	0.29	77.0	4.53
1575	0.57	0.29	77.3	4.52
1580	0.57	0.29	77.5	4.52
1590	0.57	0.29	78.0	4.52
1600	0.57	0.29	78.5	4.52

Chip Information

_Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE	PACKAGE	OUTLINE	LAND
TYPE	CODE	NO.	PATTERN NO.
6 WLP	W61B1+1	21-0217	

PROCESS: SiGe BiCMOS

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	9/10	Initial release	_

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

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